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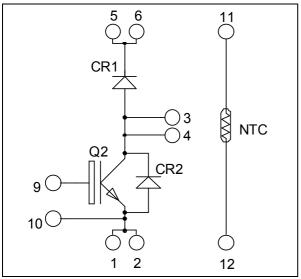
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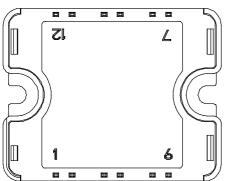
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Boost chopper Trench + Field Stop IGBT3 Power Module





Pins 1/2; 3/4; 5/6 must be shorted together

$V_{CES} = 600V$ $I_C = 75A$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

| Symbol | Parameter | | Max ratings | Unit |
|------------------|---|----------------------------------|-------------|------|
| V _{CES} | Collector - Emitter Breakdown Voltage | | 600 | V |
| т | Continuous Collector Current | $T_C = 25^{\circ}C$ | 100 | |
| IC | I _C Continuous Collector Current | $T_C = 80^{\circ}C$ | 75 | Α |
| I _{CM} | Pulsed Collector Current | $T_C = 25^{\circ}C$ | 140 | |
| V _{GE} | Gate – Emitter Voltage | | ±20 | V |
| PD | Maximum Power Dissipation | $T_C = 25^{\circ}C$ | 250 | W |
| RBSOA | Reverse Bias Safe Operating Area | $T_{\rm J} = 150^{\circ}{\rm C}$ | 150A @ 550V | |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

| Electrical Characteristics | | | | | | | | | |
|----------------------------|--------------------------------------|------------------------------------|------------------------|-----|-----|-----|------|--|--|
| Symbol | Characteristic | Test Conditions | | Min | Тур | Max | Unit | | |
| I _{CES} | Zero Gate Voltage Collector Current | $V_{GE} = 0V, V_{CE} = 600V$ | | | | 250 | μΑ | | |
| V _{CE(sat)} | Collector Emitter Saturation Voltage | $V_{GE} = 15V$ | $T_j = 25^{\circ}C$ | | 1.5 | 1.9 | V | | |
| V CE(sat) | Concetor Emitter Saturation Voltage | $I_C = 75A$ | $T_{j} = 150^{\circ}C$ | | 1.7 | | v | | |
| V _{GE(th)} | Gate Threshold Voltage | $V_{GE} = V_{CE}, I_C = 600 \mu A$ | | 5.0 | 5.8 | 6.5 | V | | |
| I _{GES} | Gate – Emitter Leakage Current | $V_{GE} = 20V, V_{CE} = 0V$ | | | | 600 | nA | | |

Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min | Тур | Max | Unit | | |
|---------------------|--|---|---|-----|------|------|------|--|
| Cies | Input Capacitance | $V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$ | | | 4620 | | | |
| C _{oes} | Output Capacitance | | | | 300 | | pF | |
| C _{res} | Reverse Transfer Capacitance | | | | 140 | | | |
| T _{d(on)} | Turn-on Delay Time | Inductive Switching (25°C) | | | 110 | | | |
| Tr | Rise Time | $V_{GE} = \pm 15V$ | | | 45 | | | |
| T _{d(off)} | Turn-off Delay Time | $V_{Bus} = 300V$ $I_C = 75A$ | $V_{Bus} = 300V$ $L_{a} = 75 \Delta$ | | 200 | | ns | |
| T _f | Fall Time | $R_G = 4.7\Omega$ | | | 40 | | | |
| T _{d(on)} | Turn-on Delay Time | Inductive Switch $V_{GE} = \pm 15V$ | ning (150°C) | | 120 | | | |
| Tr | Rise Time | $V_{\text{GE}} = 300 \text{V}$ | | | 50 | | ns | |
| T _{d(off)} | Turn-off Delay Time | $I_C = 75A$ | | | | 250 | | |
| T _f | Fall Time | $R_G = 4.7\Omega$ | | | 60 | | | |
| Б | E_{on} Turn-on Switching Energy $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ | | $T_j = 25^{\circ}C$ | | 0.35 | | mJ | |
| Lon | | | $T_{j} = 150^{\circ}C$ | | 0.6 | | 1115 | |
| Б | Turn-off Switching Energy | $I_{\rm C} = 75 \text{A}$ | $T_j = 25^{\circ}C$ | | 2.2 | | mJ | |
| E_{off} | rum-on Switching Energy | $R_G = 4.7\Omega$ | $T_{j} = 150^{\circ}C$ | | 2.6 | | 111J | |

Chopper diode ratings and characteristics

| Symbol | Characteristic | Test Conditions | | Min | Тур | Max | Unit |
|------------------|--|---------------------------------------|------------------------|------------------------|------|-----|------|
| V _{RRM} | Maximum Peak Repetitive Reverse Voltage | | | 600 | | | V |
| I _{RM} | Maximum Reverse Leakage Current | V _R =600V | $T_j = 25^{\circ}C$ | | | 250 | μA |
| *KM | Thanking the verse Dealage Carton | V _K 000 V | $T_{j} = 150^{\circ}C$ | | | 500 | μΠ |
| I _F | DC Forward current | | $Tc = 80^{\circ}C$ | | 75 | | А |
| V _F | Diode Forward Voltage | $I_{\rm F} = 75 A$ $V_{\rm GE} = 0 V$ | $T_i = 25^{\circ}C$ | | 1.6 | 2 | |
| • F | Diode Forward Voluge | | $T_i = 150^{\circ}C$ | | 1.5 | | V |
| t _{rr} | Reverse Recovery Time | 1 754 | $T_j = 25^{\circ}C$ | | 100 | | ns |
| ۹r | Reverse Receivery Time | | $T_{j} = 150^{\circ}C$ | | 150 | | 115 |
| 0 | Reverse Recovery Charge $V_R = 300V$ $I_j = 25^{\circ}C$ | | $T_j = 25^{\circ}C$ | | 3.6 | | μC |
| Q _{rr} | | | | $T_{j} = 150^{\circ}C$ | 7.6 | 7.6 | |
| Er | Reverse Recovery Energy | | $T_i = 25^{\circ}C$ | | 0.85 | | mJ |
| Lr | Reverse Recovery Energy | | $T_{j} = 150^{\circ}C$ | | 1.8 | | IIIJ |



Thermal and package characteristics

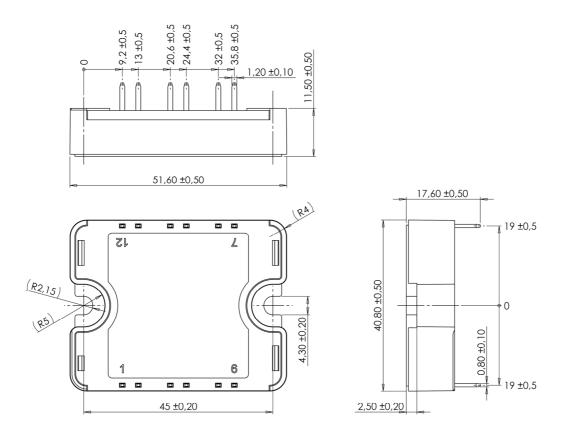
| Symbol | Characteristic | | | Min | Тур | Max | Unit |
|-------------------|---|-------------|----|------|------|------|------|
| R_{thJC} | Junction to Case Thermal Resistance IGBT Diode | IGBT | | | 0.60 | °C/W | |
| | | Diode | | | 0.98 | C/ W | |
| V _{ISOL} | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz | | | 4000 | | | V |
| T _J | Operating junction temperature range | | | -40 | | 175 | |
| T _{STG} | Storage Temperature Range | | | -40 | | 125 | °C |
| T _C | Operating Case Temperature -40 100 | | | | | | |
| Torque | Mounting torque | To heatsink | M4 | 2 | | 3 | N.m |
| Wt | Package Weight | | | | | 80 | g |

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol | Characteristic | Min | Тур | Max | Unit |
|-----------------|-----------------------------|-----|------|-----|------|
| R ₂₅ | Resistance @ 25°C | | 50 | | kΩ |
| B 25/85 | $T_{25} = 298.15 \text{ K}$ | | 3952 | | K |

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

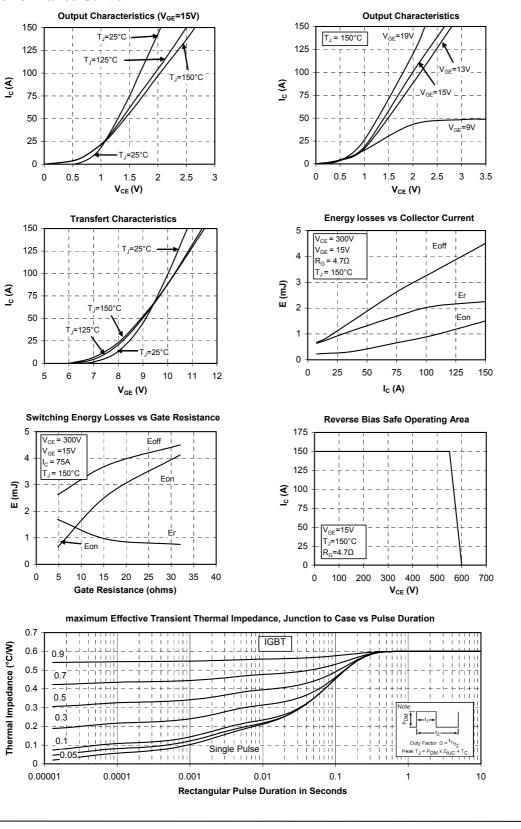
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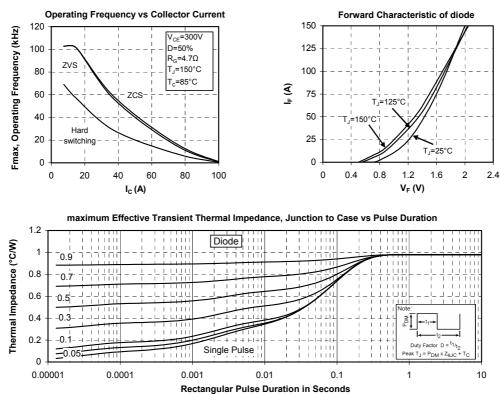
Typical Performance Curve

APTGT75DA60T1G



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